Results of GaAs:Cr and Si sensors irradiated by 20 MeV electron beam

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on behalf of the JINR group

FCAL Collaboration
High precision design

JOINT INSTITUTE FOR NUCLEAR RESEARCH
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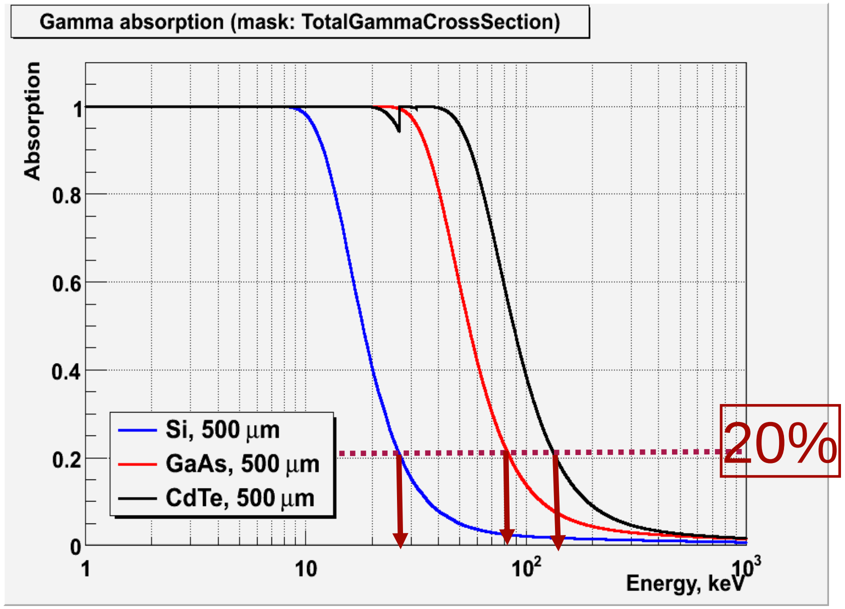
Gallium arsenide as a detector material

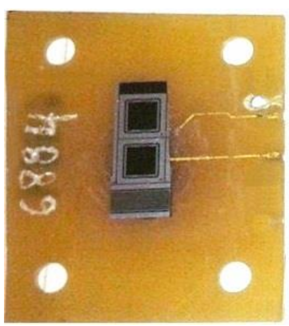
- GaAs is a well-known semiconductor, second widespread after silicon
- Limited use in particle detection because of low resistivity, low CCE and high intrinsic noise
- New modification of GaAs, compensated by Cr (GaAs:Cr), has been invented in Tomsk State University in 2000-2005
  - suitable for detector construction
  - radiation hard
  - Z(GaAs)~ 32 vs Z(Si)=14 → higher photon detection efficiency



Material	main charge carriers	electron drift length	bulk resistivity	active sensor thickness	intrinsic noise
LEC SI-GaAs	holes	0.3-0.5 mm	$<2*10^8$ Ω*cm	<300 μm	high
GaAs:Cr	electrons	0.7 – 2 mm	$\sim 10^9$ Ω*cm	up to 1 mm	low

GaAs:Cr and Si sensors

N	Type	Producer	Holder	Size, x y z, mm^3	Sensitive area, mm^2
1	GaAs:Cr (n^+-π-ν-n) barrier	TSU (Tomsk, Russia)	Plastic	5x5x0.3	5x5
2	GaAs:Cr high resistive	TSU (Tomsk, Russia)	PCB	5x5x0.3	4.5x4.5
3	Si *(p^+nn^+)* n-type 1	RIMST (Zelenograd, Russia)	Plastic	5x5x0.25	13
4	Si n-type 2	Hamamatsu HPK(USCS, USA)	PCB	10x10x0.4	3.5x3.5



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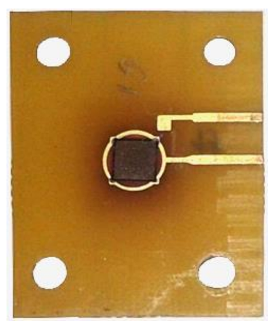

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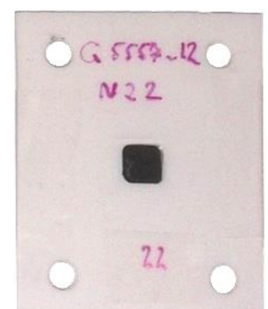

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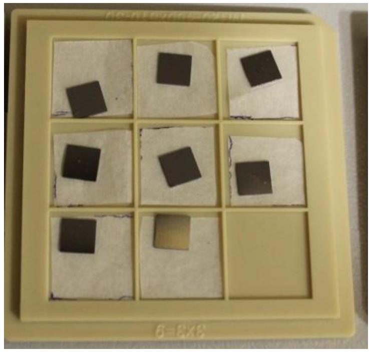
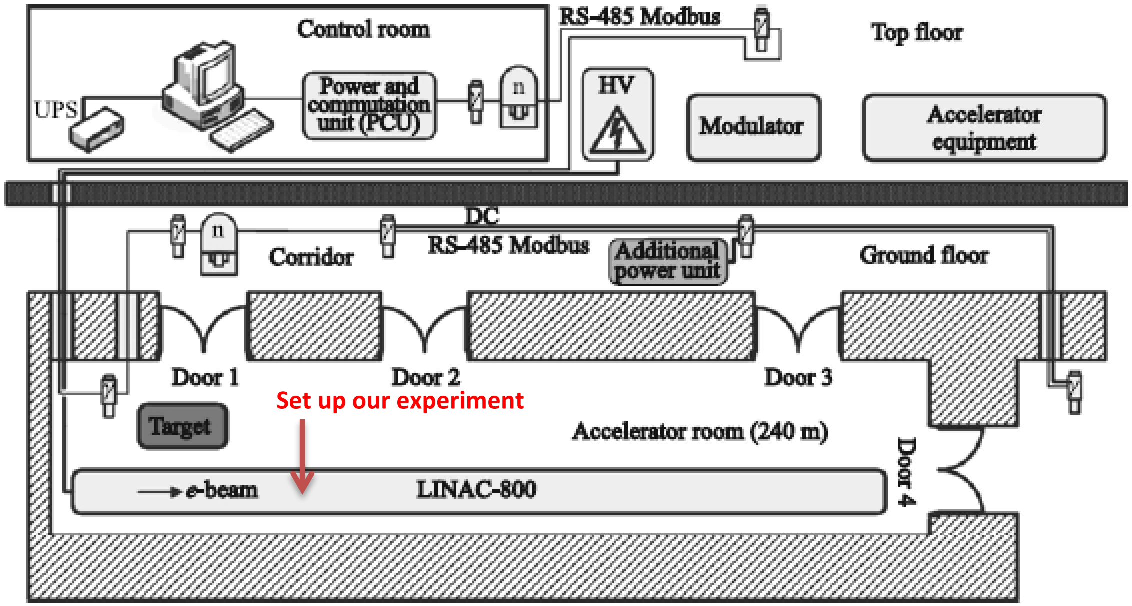


1

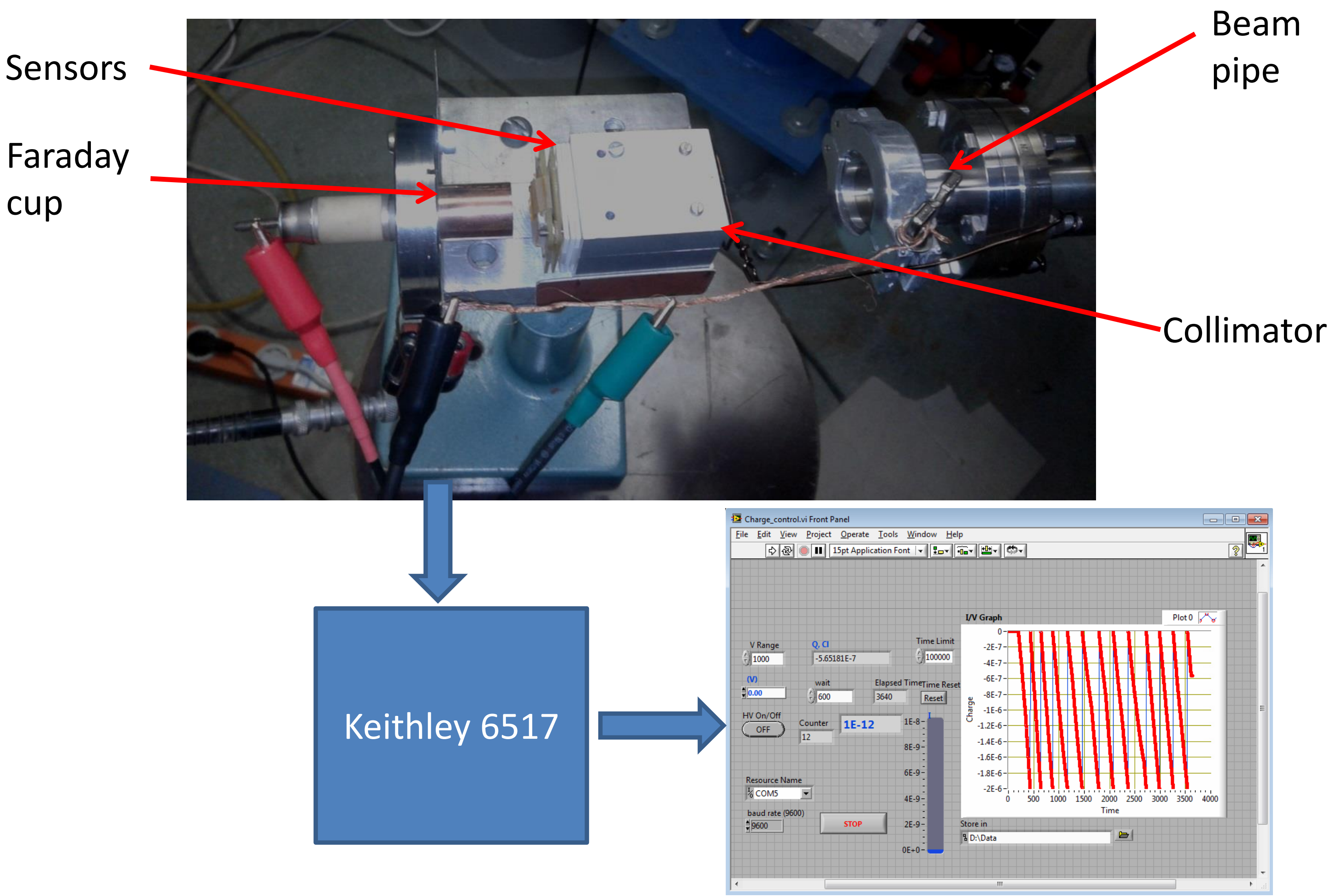
LINAC-800 e⁻ accelerator



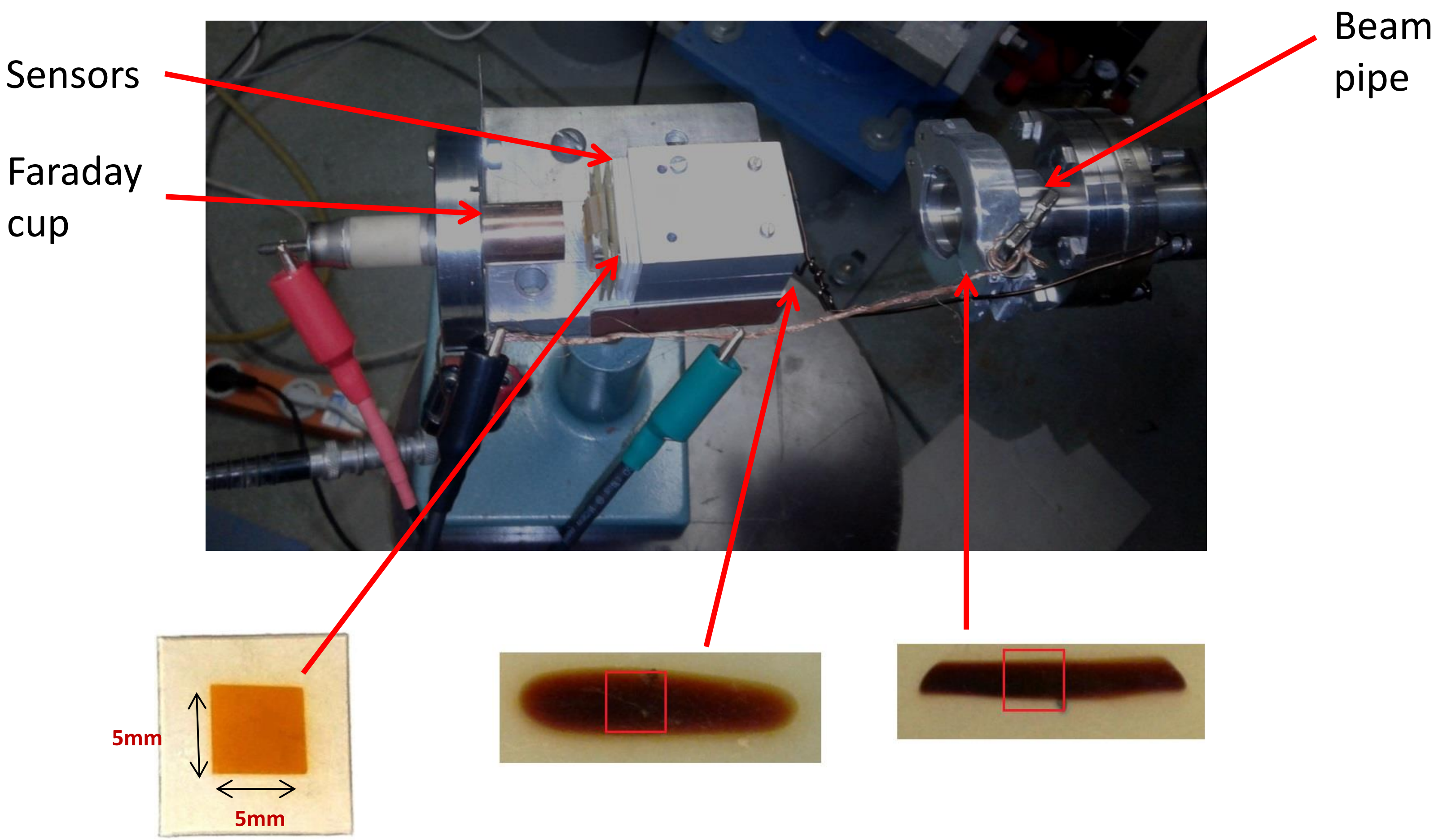
800 MeV electron linear accelerator (LINAC-800) is under construction at JINR. 20 MeV beam channel was used for sensors irradiation. Beam parameters:

- bunch current up to 10 mA,
- duration 2 μs,
- frequency from 1 to 10 Hz.

Irradiation setup



Irradiation beam control

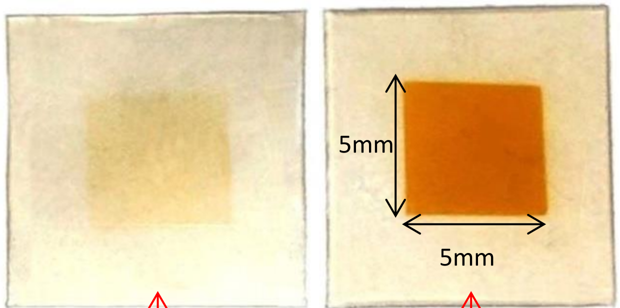


GEANT 4 simulation

The electron transport through the irradiation setup was simulated by GEANT4 in order to obtain the ratio of registered by Faraday cup charge to absorbed dose for all types of sensors.

Configuration	Holder	Thickness [µm]	Absorbed dose to charge in Faraday cup [kGy/µC]		Error ,%
			1-st sensor	2-nd sensor	
GaAs (1)	Plastic	300	4.99	-	2.8
GaAs (2)	PCB	300	4.99	-	2.8
Si type1 (3)	Plastic	250	5.61	-	1.4
Si type2 (4)	PCB	400	5.68	-	1.4
(1)+ (1)	Plastic	-	5.14	4.87	2.7 – 2.8
(2)+ (4)	PCB	-	5.19	5.51	2.7 - 1.4

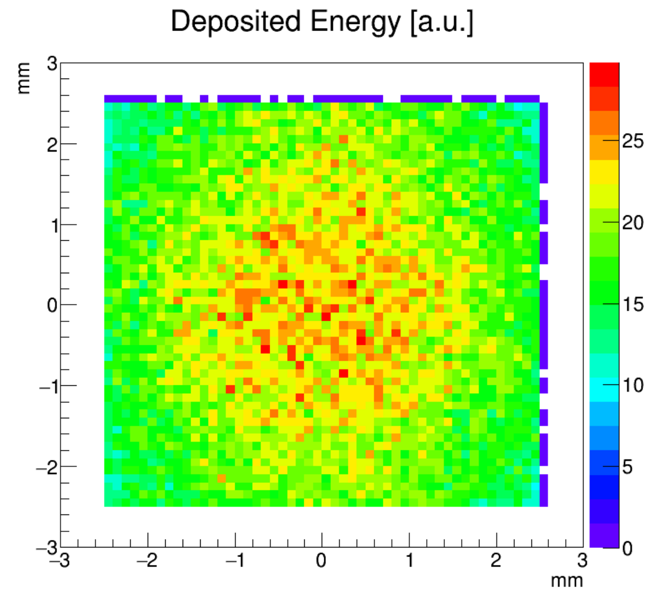
Irradiation control



48 kGy
(2.1×10^{14} e^-/cm^2)

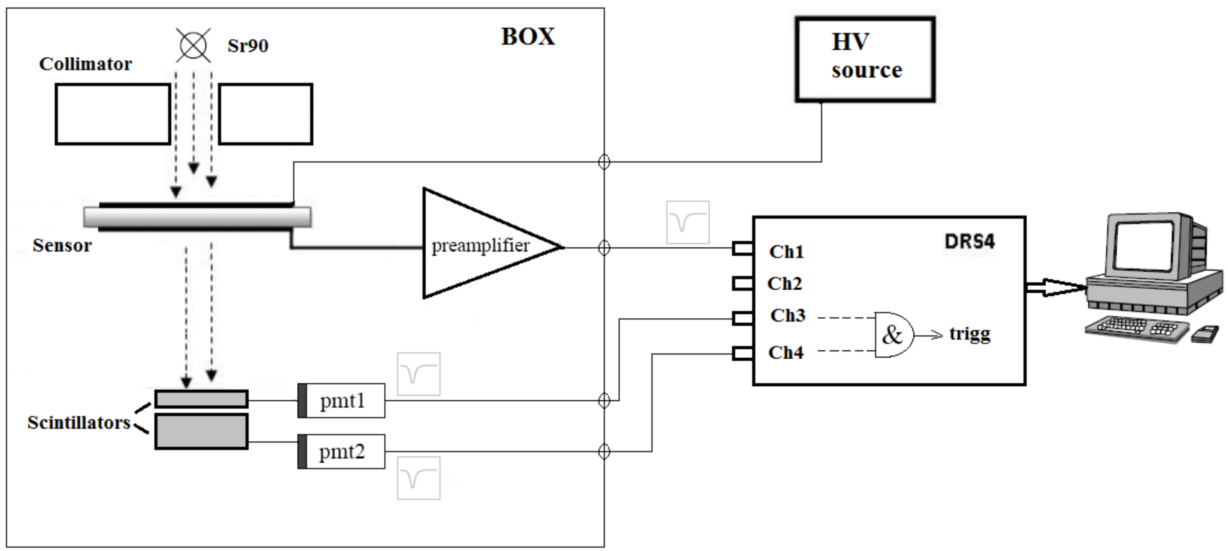
194 kGy
(8.4×10^{14} e^-/cm^2)

The radiation sensitive film was placed behind the sensor to control the absorbed dose, and the uniformity of electron flounce during irradiation.



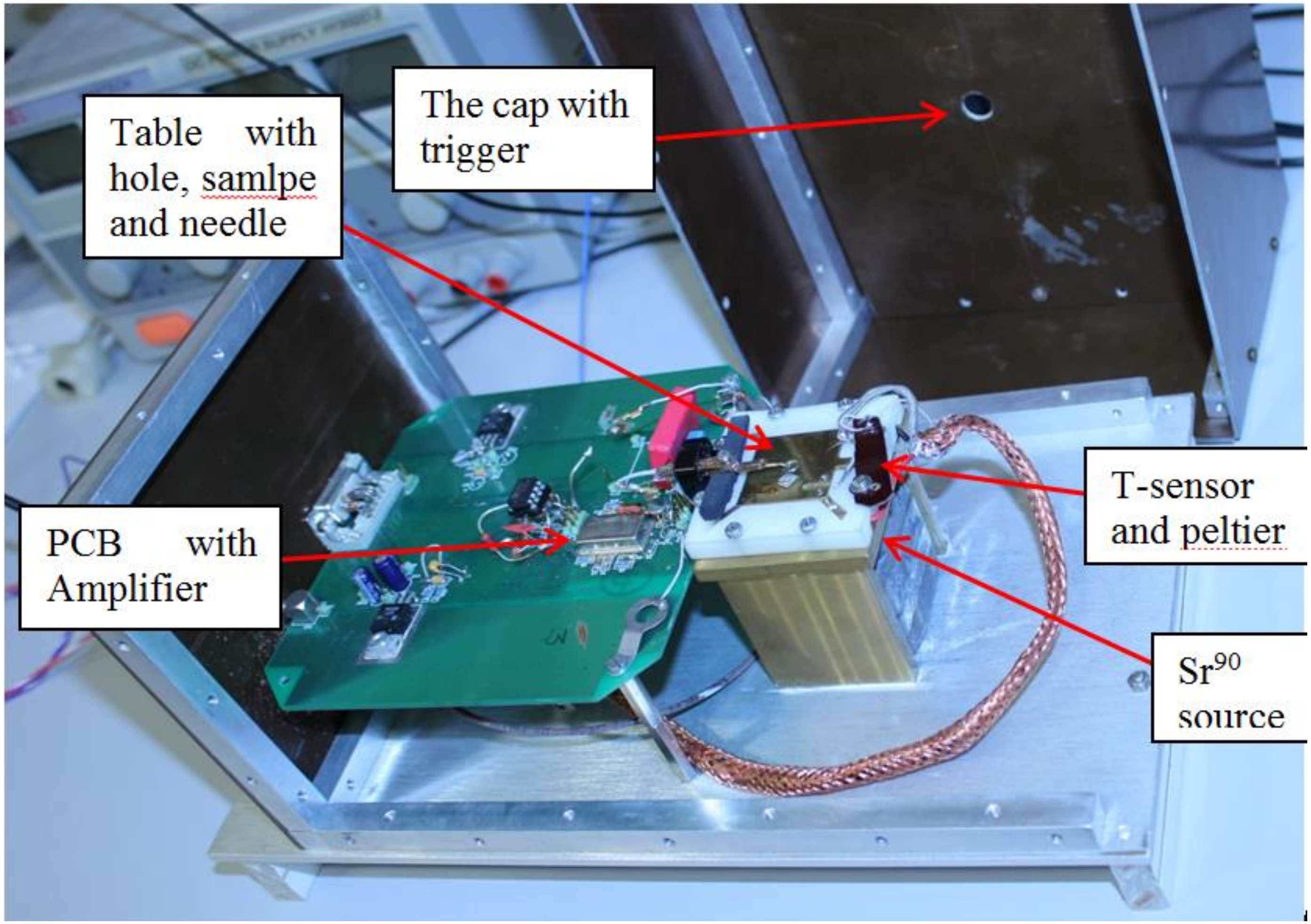
GEANT 4 simulation for the distribution of the deposited energy over the GaAs sensor 5x5x0.3 mm^2 area in e^--beam after collimator. Statistics 2×10^6 e^-

CCE(Charge collection efficiency) measurement setup



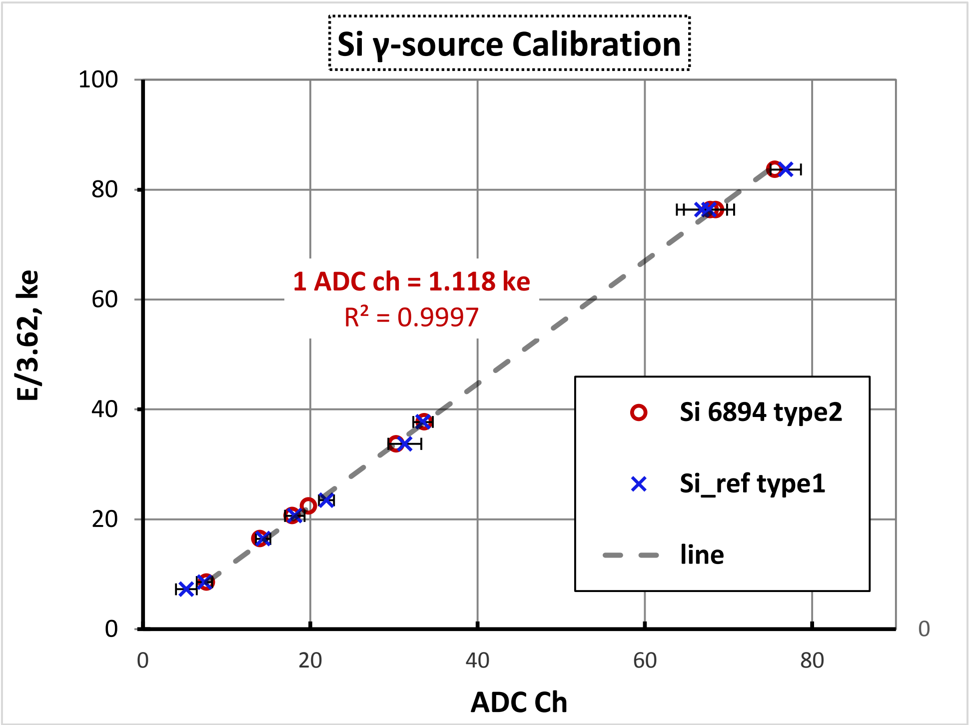
electrons from Sr^{90} source well collimated and triggered by 2 scintillators. It allows to cut and measure signal only from electrons passed throw the sensor with energy from 1 to 2.2 MeV which is close to MIP electrons

Installation for CCE and I-V measurement



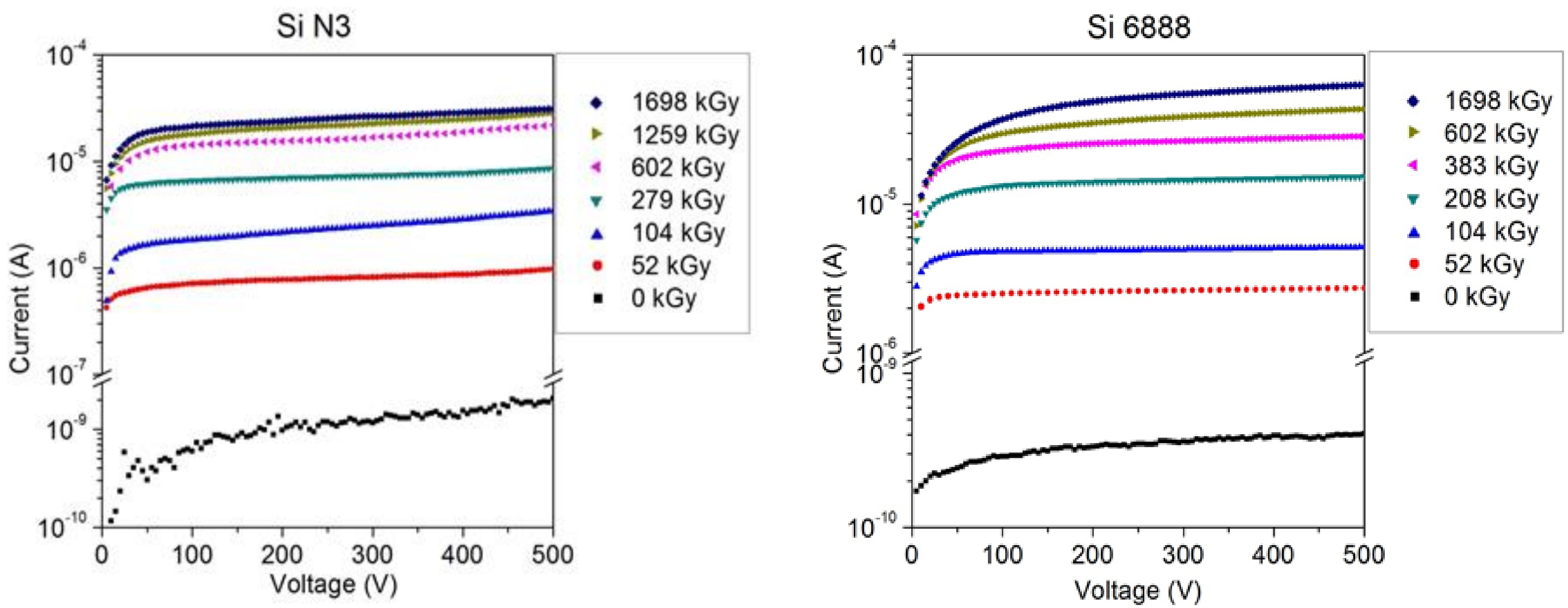
All the sensors measured at room temperature, except some measurements at low temperature for Si

Installation for CCE and I-V measurement



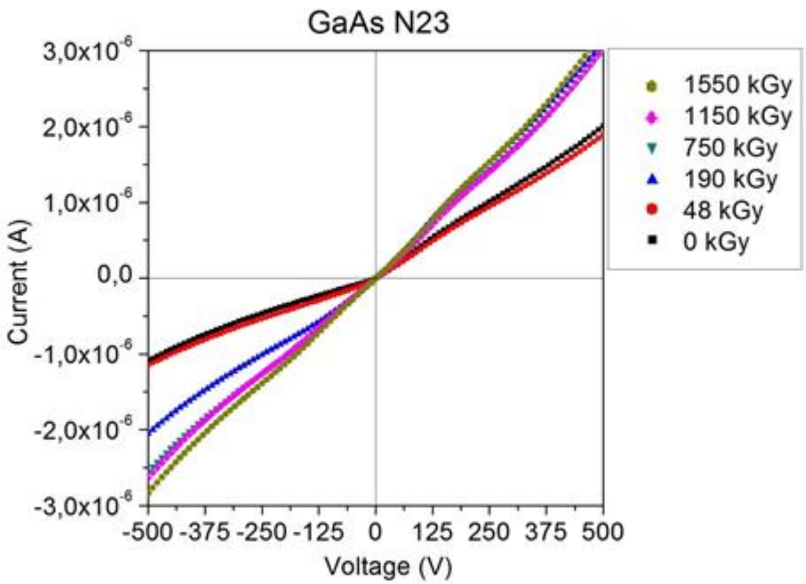
Measurement setup was calibrated by Am^{241} , Am^{243} , Ba^{133} , Co^{57} γ-sources
Energy diapason from 26 to 303 keV for both types of Si sensors.

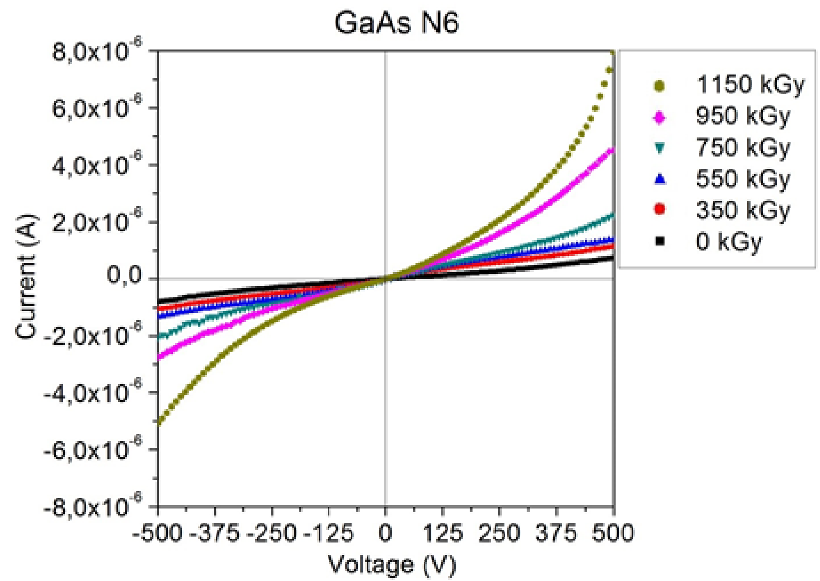
Results I-V Si



I-V characteristics of the normal n-type Si (N3) and radiation hard USCS Si (6888).
The dark current increased almost 4 orders of magnitude after the absorbed dose of 1.6 MGy

Results I-V GaAs:Cr: πν junction and HR

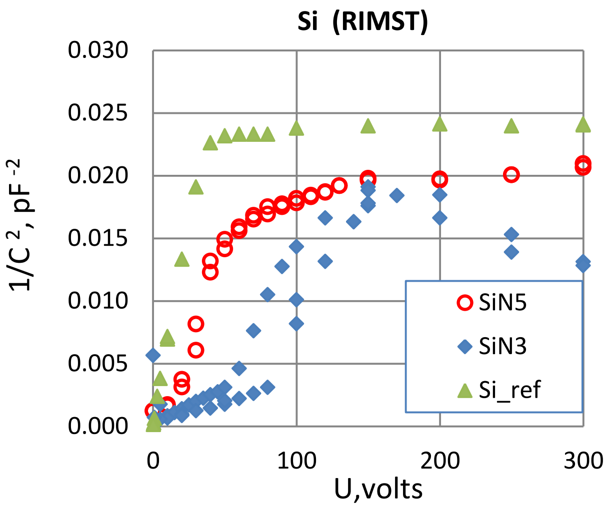


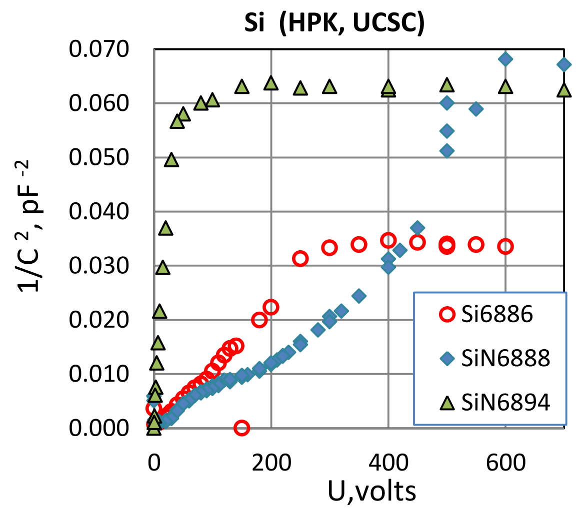


I-V characteristics before and after irradiation with different doses for high resistive GaAs:Cr (left) and barrier GaAs:Cr (right) sensors.

Resistivity of GaAs:Cr sensors is about 2-5*10^9 Ohm*cm, the dark current increased only 3 times for the high resistive and 4-5 times for the barrier GaAs:Cr.

C-V



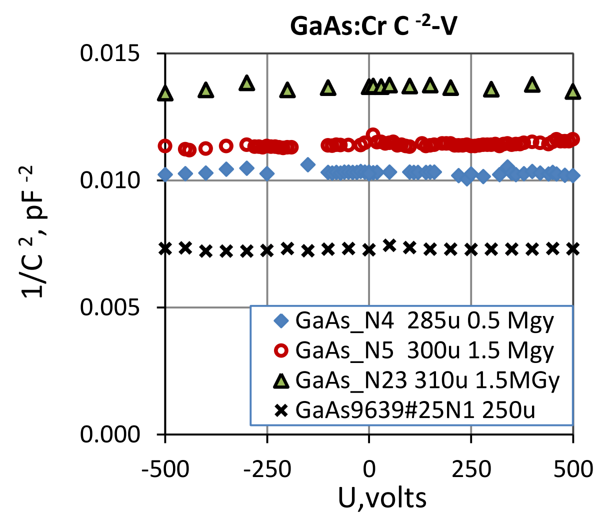


C^{-2}-V for Si type1(left) Si type2 (right) GaAs:Cr (down):

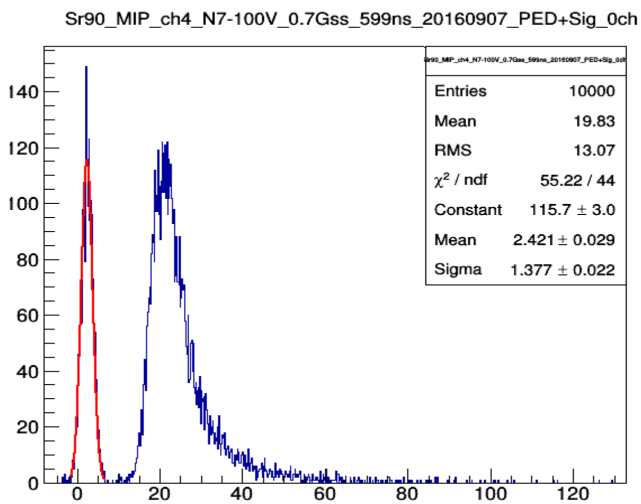
Unirradiated Si_ref, Si_6894 U_{fd}<40V;

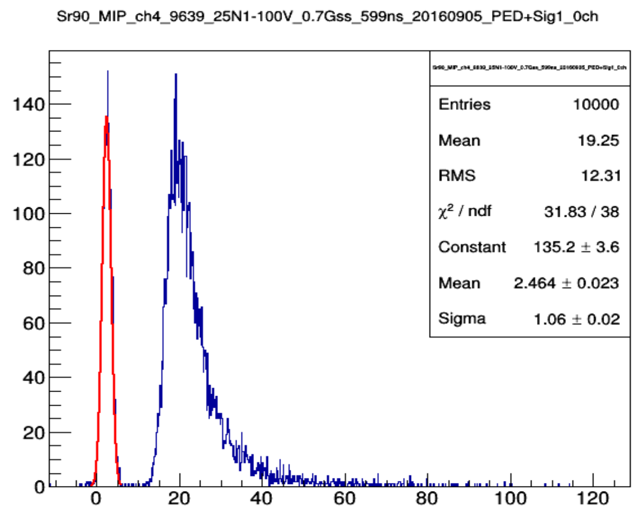
0.5 MGy Si_N5(type1) U_{fd}=100V;
Si_6886(type2) U_{fd}=300V;
GaAs:Cr_N4 (barrier)

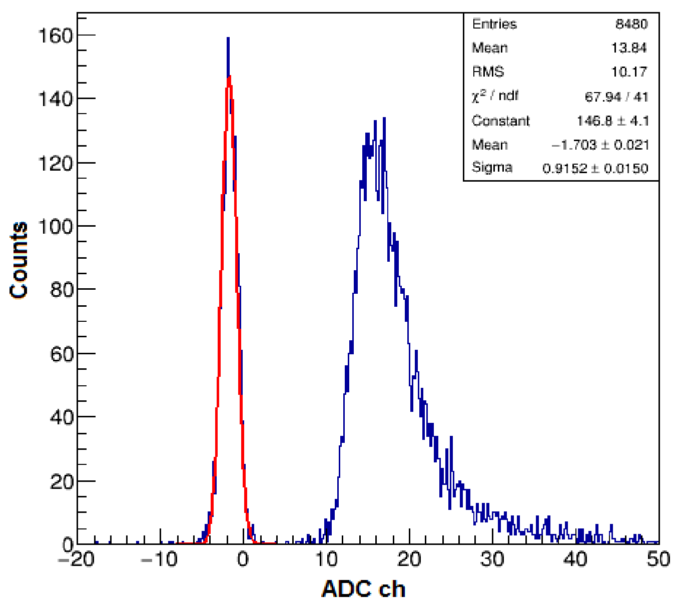
1.5 Mgy Si_N5(type1) U_{fd}=150V
Si_6888(type2) U_{fd} >600V;
GaAs:Cr_N5 – barrier type;
GaAs:Cr N23 – high resistive type;



MIP spectra for GaAs and Si sensors before irradiation





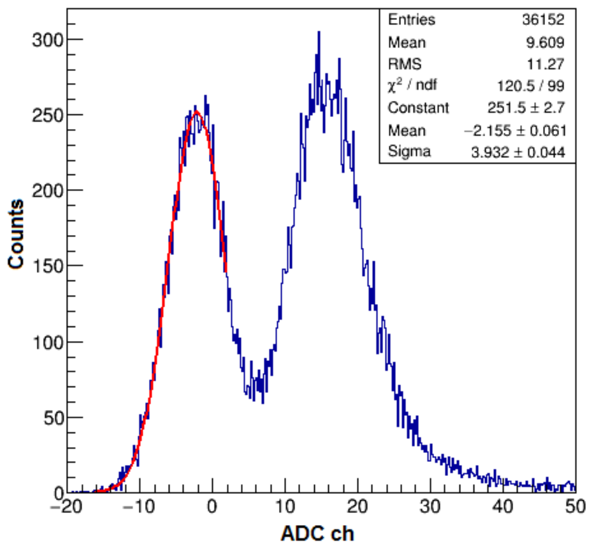


MIP spectrum from Sr^{90} ß-source for sensors, measured with Ubias =100V:

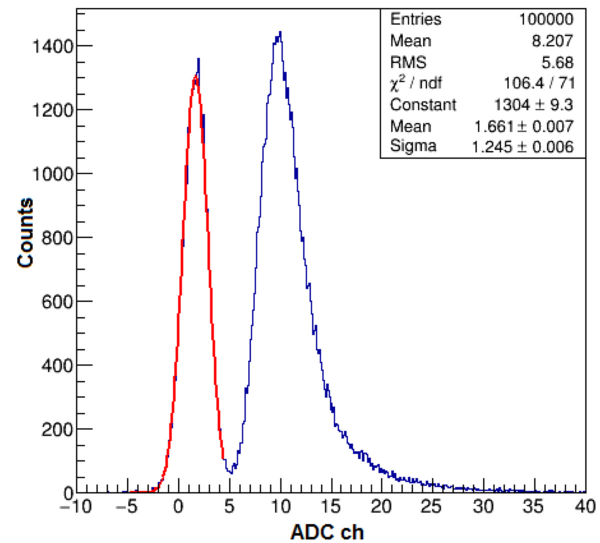
- *HR GaAs:Cr (left)*
- πν-junction *GaAs:Cr (right)*
- *Si type1 (down)*

MIP for Si & GaAs:Cr after 0.5 MGy

Type 1 Si_N5; 602kGy ; T= 16°C



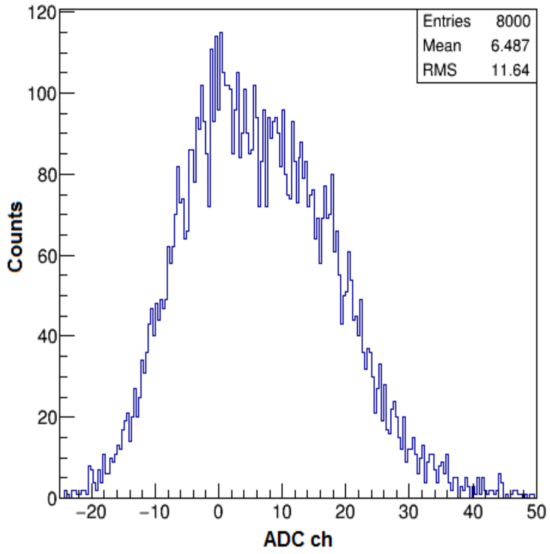
Barrier GaAs_N4: 550kGy ; T =22°C



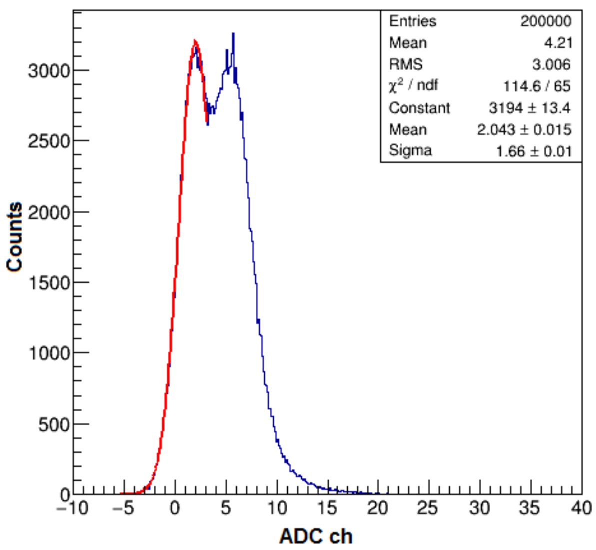
A slight cooling of the sensor Si for 5°C improves the MIP-signal and pedestal separation, but it is still worse than GaAs:Cr.

MIP for Si & GaAs:Cr after 1.5 MGy

Type 1 Si_N3: 1.3 MGy ;
Ubias=100V: T =22°C

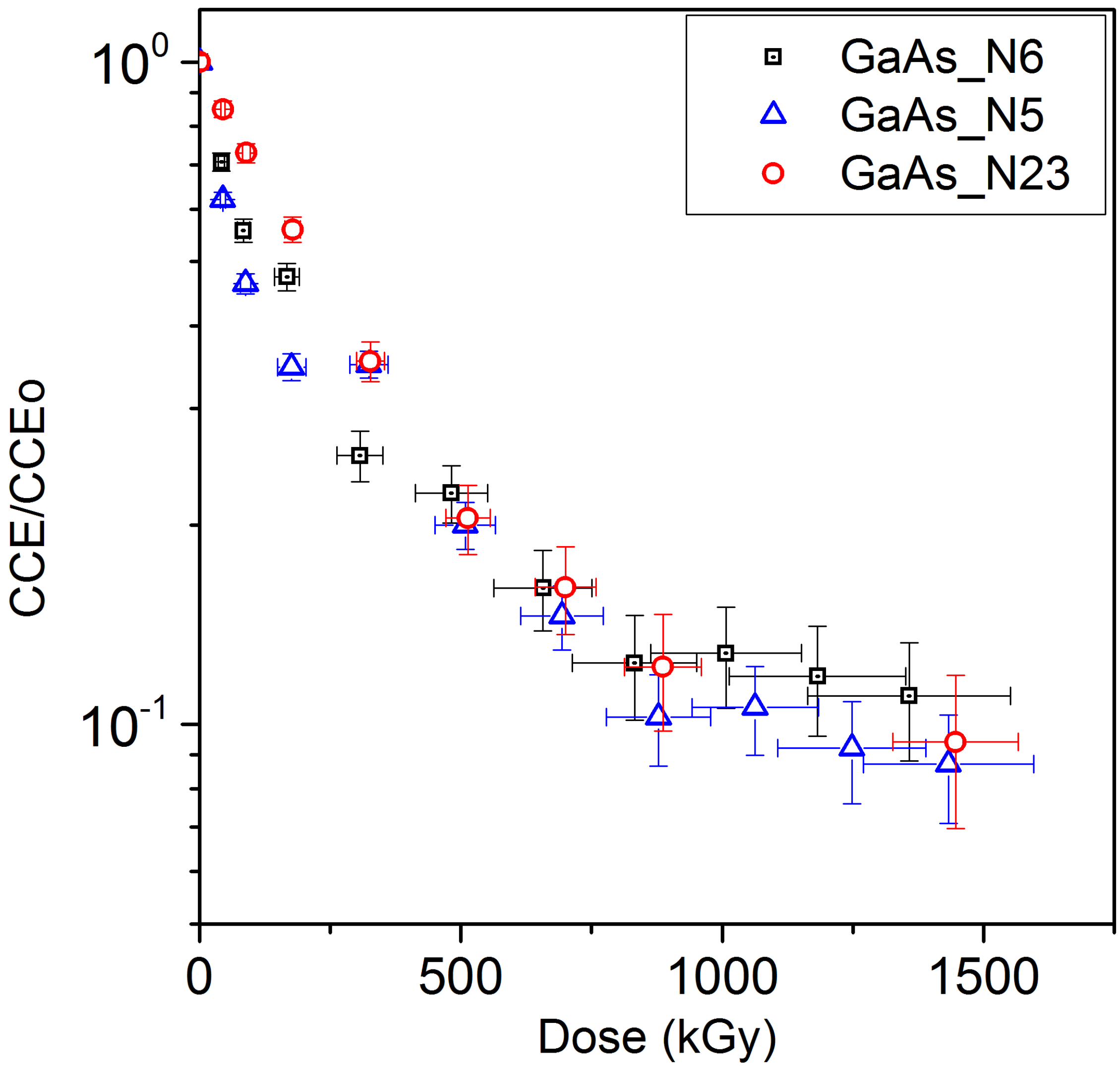


Barrier GaAs:Cr_N6: 1.5 MGy ;
Ubias=500V; T =22°C



After 1.5 MGy the MIP-signal and the pedestal are hardly separated.

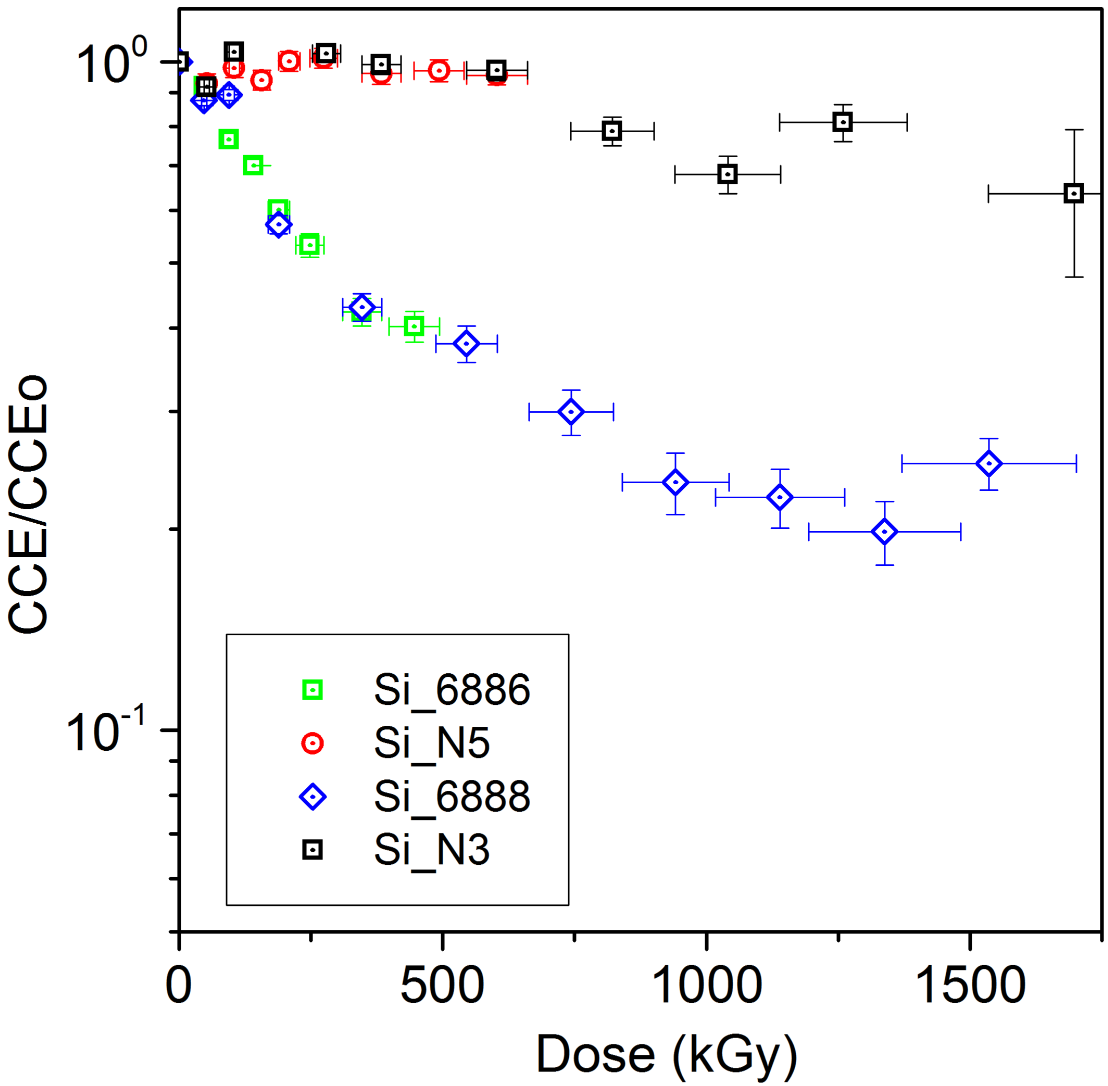
GaAs:Cr CCE vs Dose



In GaAs:Cr the CCE falls monotonously and abruptly until to dose 1MGy, but then it decreases slowly up to the maximum irradiation dose.
It was observed for both sensor types:

- N5,N6 - barrier GaAs:Cr
- N23- high resistivity GaAs:Cr

Si CCE vs Dose

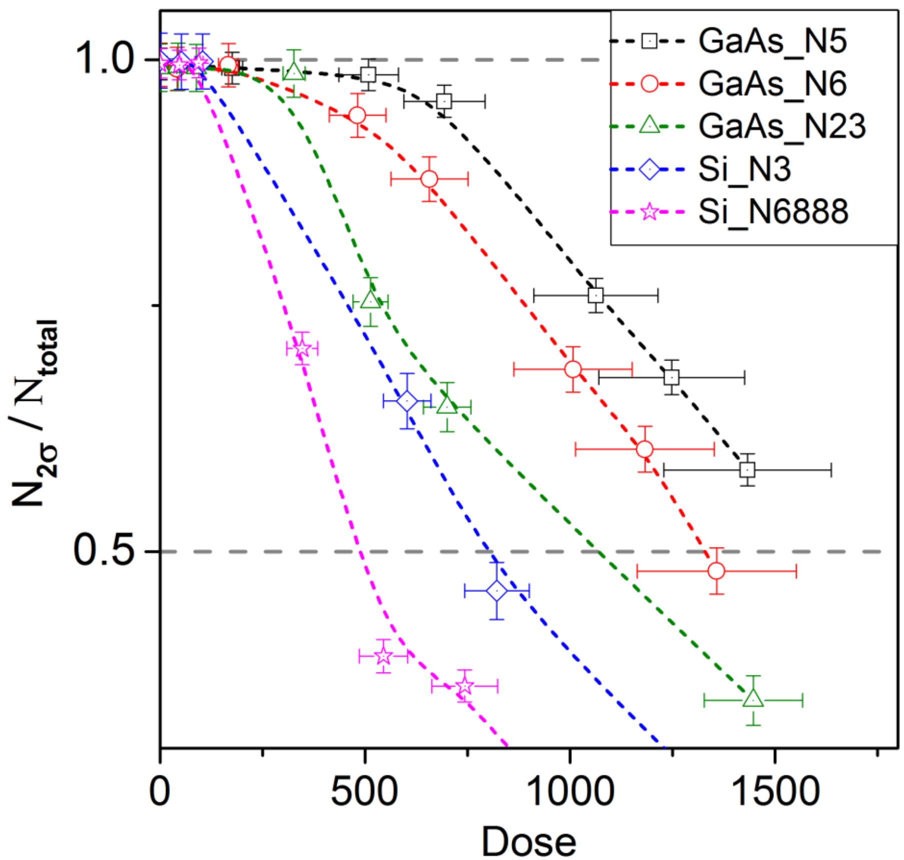


Due to increasing of the dark current the pedestal considerably broadened and the measurement becomes difficult for doses higher 0.5 MGy.

N3,N5 – Si type 1;

6886, 6888 – Si type 2;

GaAs:Cr and Si sensor resolution.



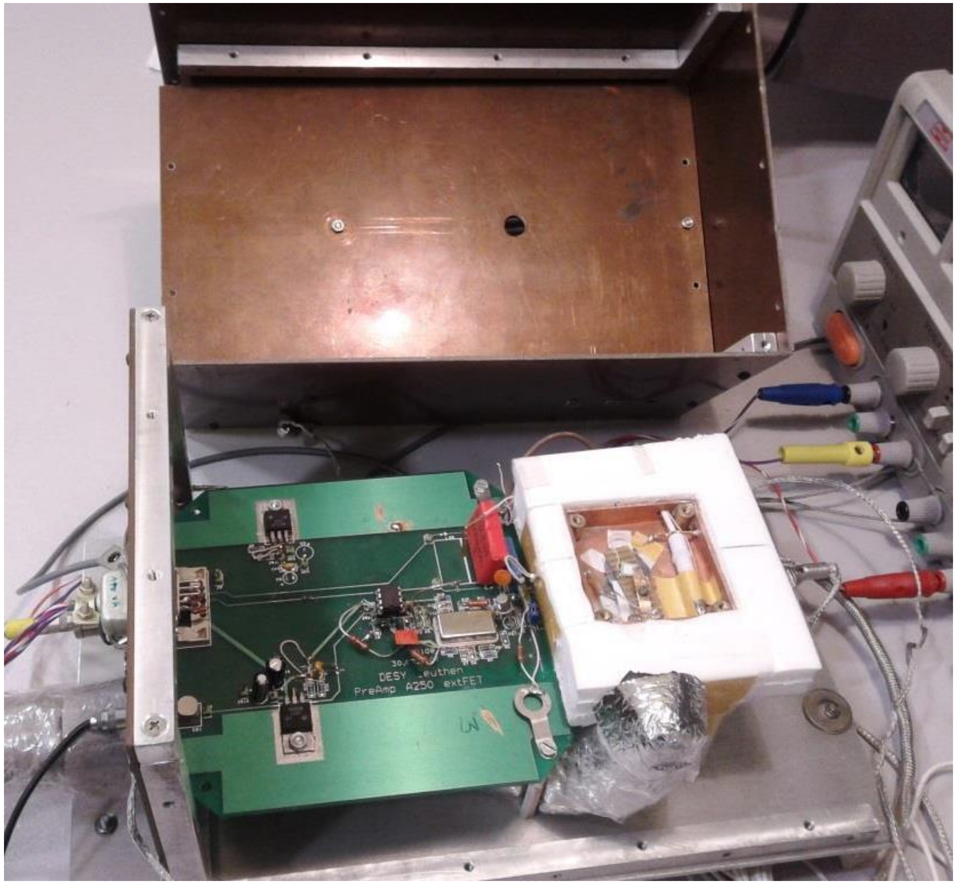
2σ-criterion was applied for a correct comparison of GaAs and Si sensors performance.

$$K = \frac{N_{2\sigma}}{N_{total}}$$

K is the ratio of events departed greater than the total number 2σ from pedestal to the total number of events in MIP-spectrum.

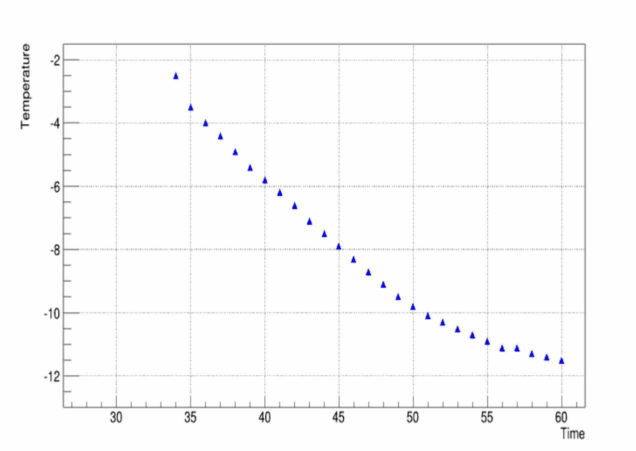
The greater ***K***, the better the signal and pedestal separation for MIP-spectrum.

Sensor cooling

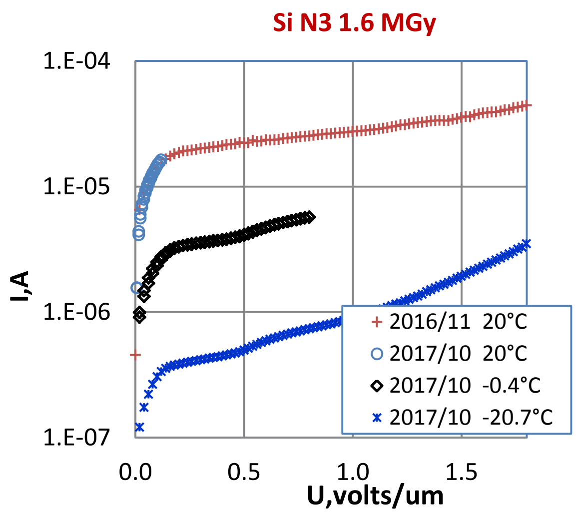


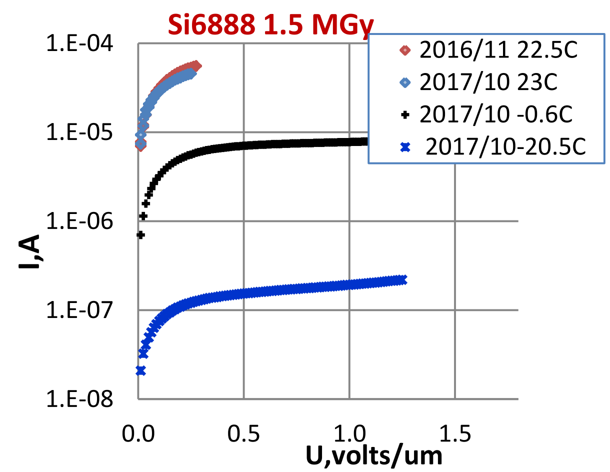
Measurement setup was modified for cooling.

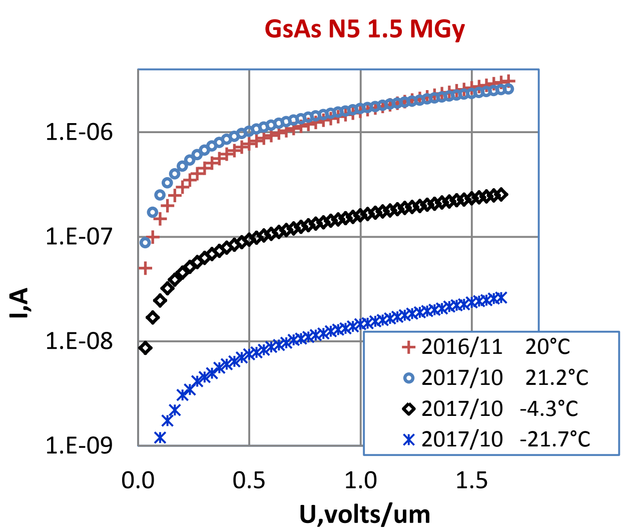
Allow to measure I-V and CCE sensors with T from room temperature to -50°C



Sensors cooling: I-V





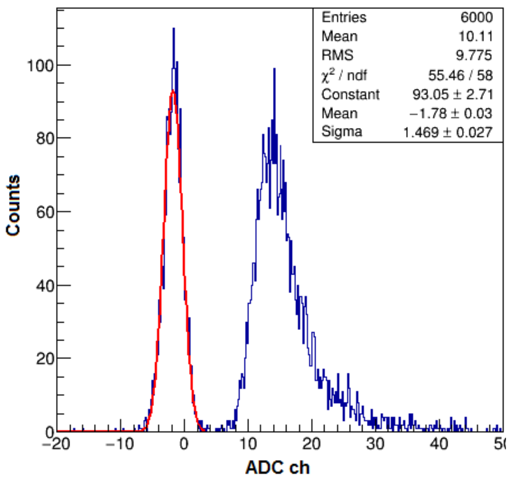


I-V characteristics, measured with different sensor temperatures:

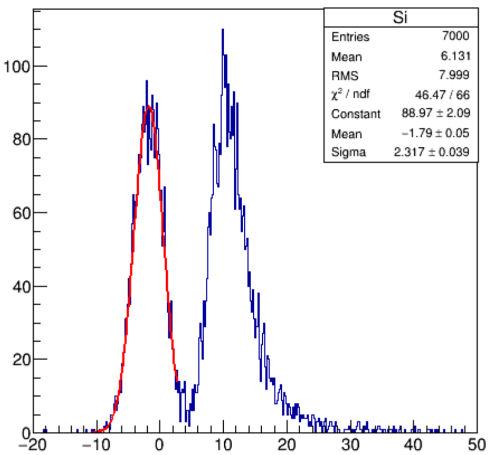
- Si_N3 (type1) 1.7 MGy
- Si_6888 (type2) 1.5 MGy
- GaAs:Cr_N5 (barrier) 1.5 MGy

Si cooling: MIP spectrum

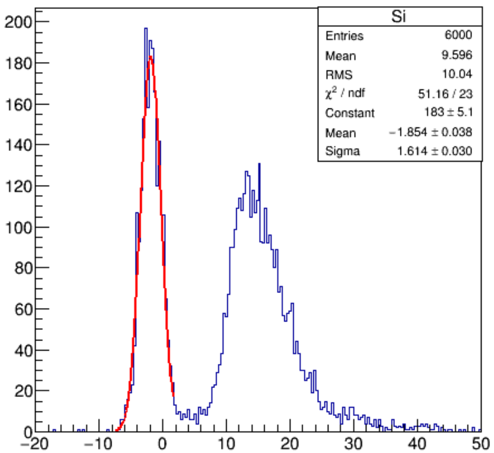
Si N5 0.6 MGy ; Ubias = 100V



Si N3 1.6 MGy ; Ubias = 100V



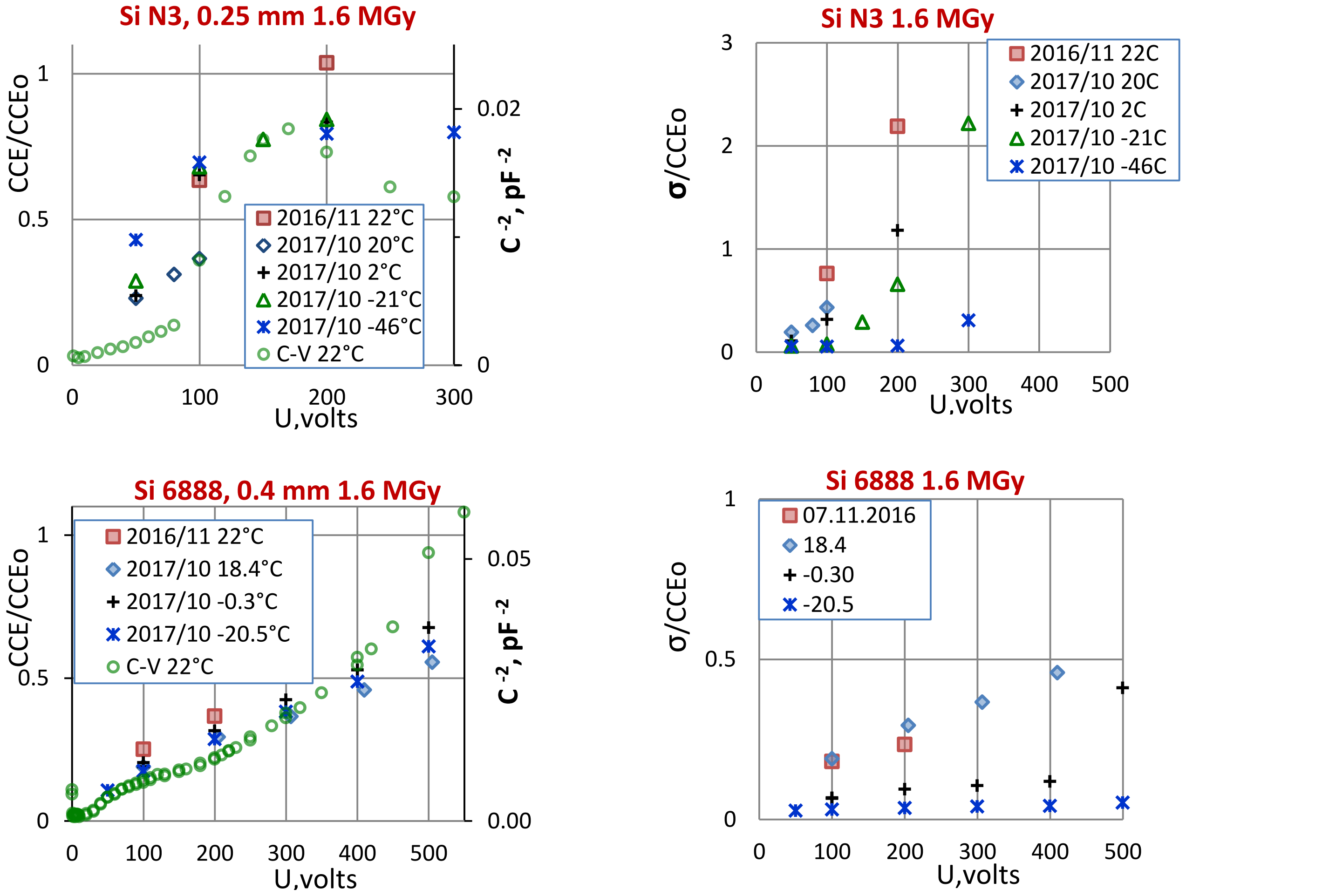
Si 6888 1.6 MGy ; Ubias = 400V



MIP spectra for Si type1: 0.6 MGy (left) 1.6 MGy (center). Type2 1.6 MGy (right).

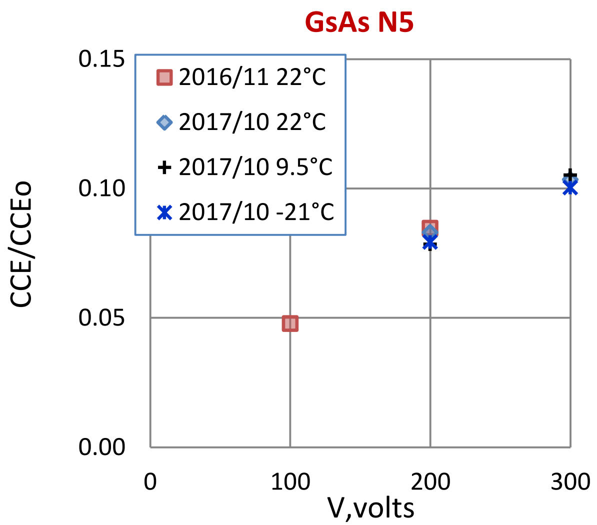
The pedestal is visible on the left. Measurement temperature **-21ºC**.

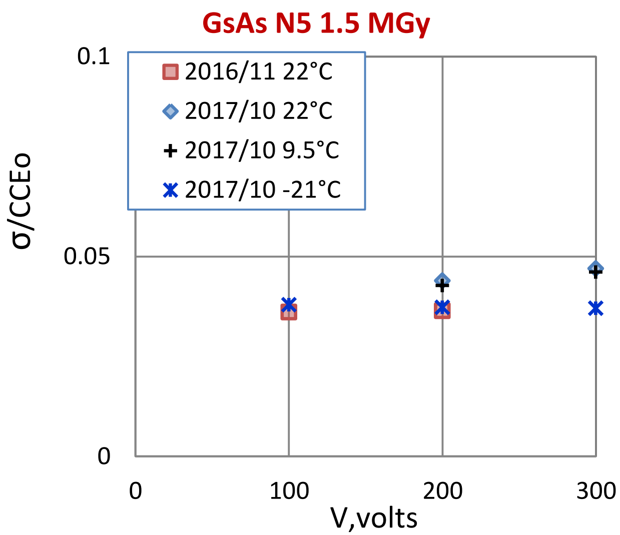
Si cooling 1.6 MGy: CCE-V, C $^{-2}$-V, σ-V



CCE, C $^{-2}$(left) and **σ** (right) as function of applied voltage for Si sensor after irradiation dose 1.6 MGy ($7x10^{15}$ e^-/sm^2). Si N3 – type1, Si 6888 – type2.

GaAs cooling 1.5 MGy: CCE-V, σ-V





CCE (left) and **σ** (right) as function of applied voltage for GaAs:Cr N5 sensor after irradiation dose 1.5 MGy ($7x10^{15}$ e^-/sm^2).

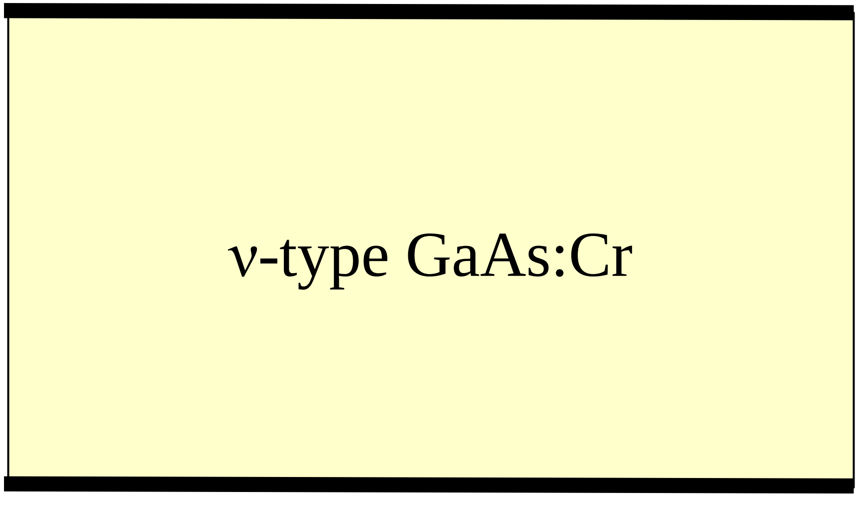
Summary

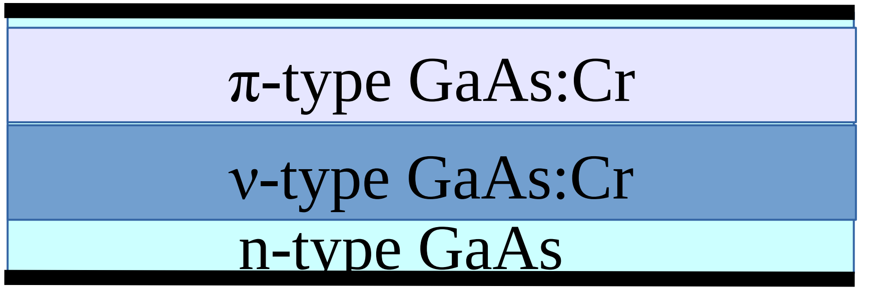
- Irradiation of the high-resistive and barrier GaAs:Cr sensors and the normal and two n-type Si sensors by 20 MeV electron beam of was performed.
- Radiation damage in GaAs and Si are different: strong increasing of the dark current in Si and dropping signal in GaAs:Cr.
- A significant difference between two types of GaAs:Cr sensors is not found.
- 2-σ criterion was applied in order to estimate irradiated sensors resolution.
- After dose 1.5 Mgy signal magnitude drops to ~10% of initial in GaAs:Cr , when Si requires cooling.
- For n-type Si U_{fd} is rising with irradiation, more strong for sensors from Hamamatsu.
- Cooling makes Si sensors usable even after absorbed dose of 1.6 MGy when for irradiated GaAs:Cr sensors there is no dependence of the signal and noise on temperature.

Backup slides

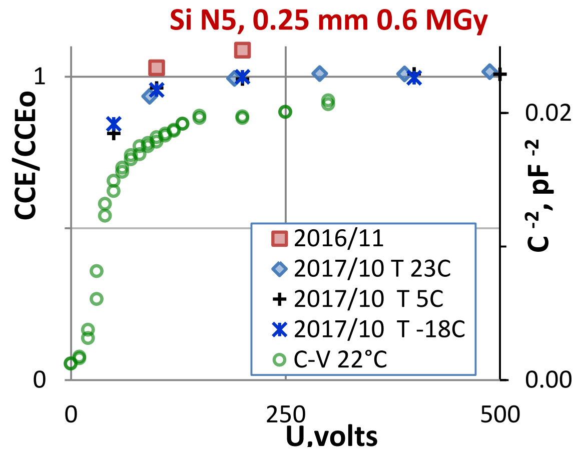
Two types of GaAs:Cr detectors

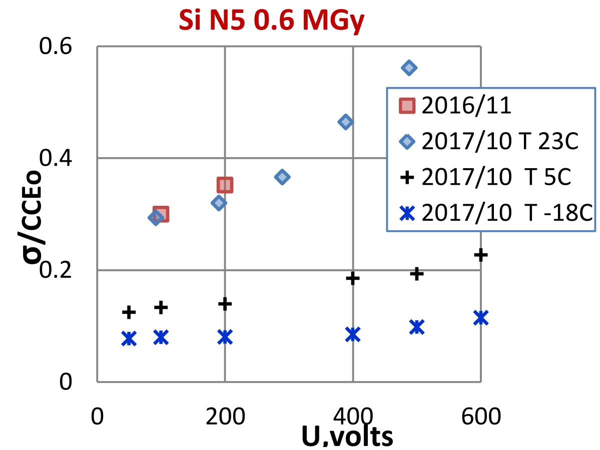
- 'High Resistive' GaAs:Cr
  - resistivity ~10^9 Om*cm
  - active thickness up to 1 mm
  - electron drift length up to 2 mm
- πν junction structure
  - active thickness is determined by πν junction (depending on Ubias)
  - resistivity and CCE are similar.

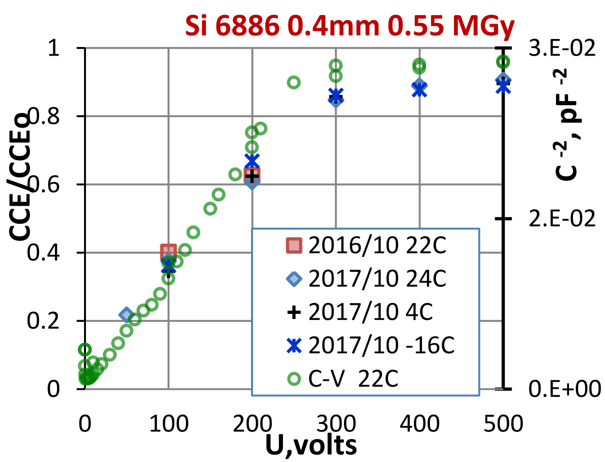


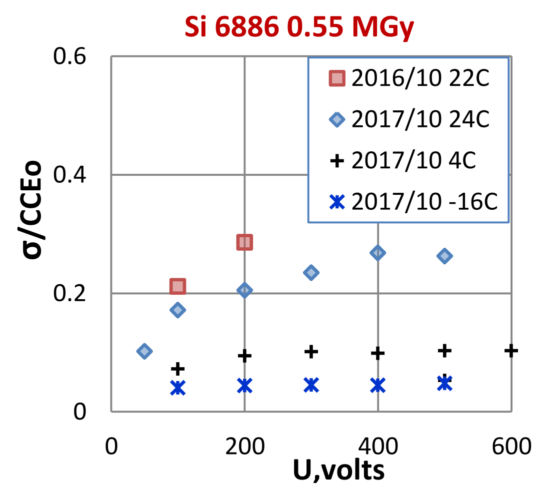


Si cooling 0.6 MGy: CCE-V, C $^{-2}$-V, σ-V



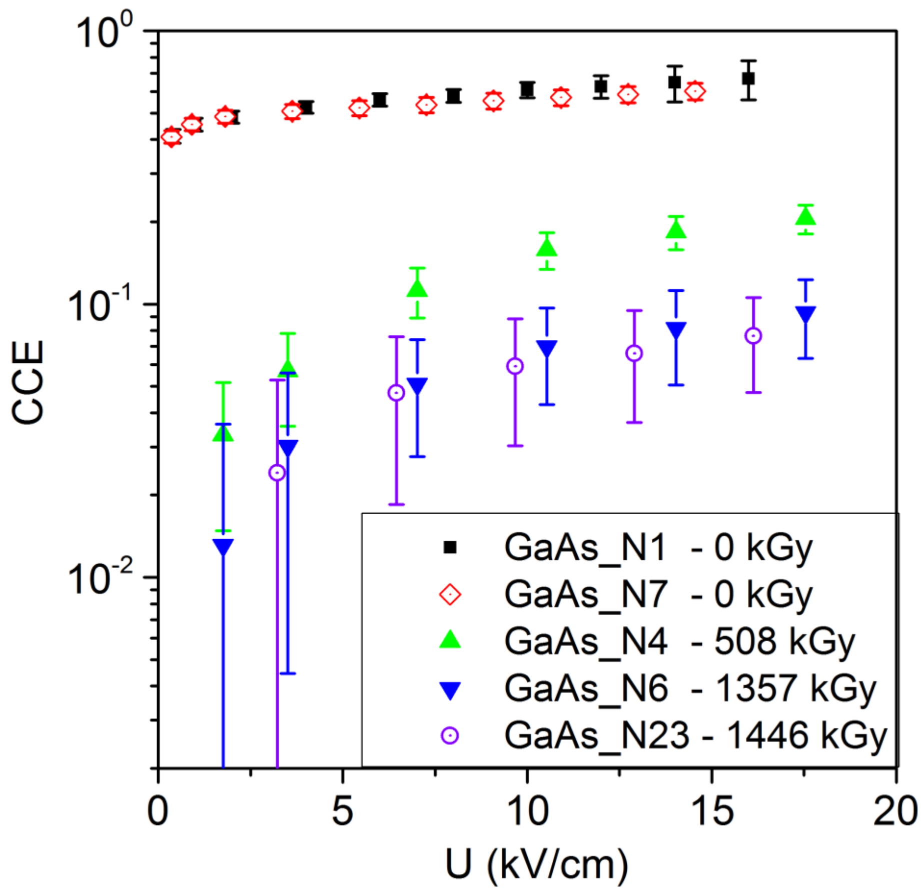






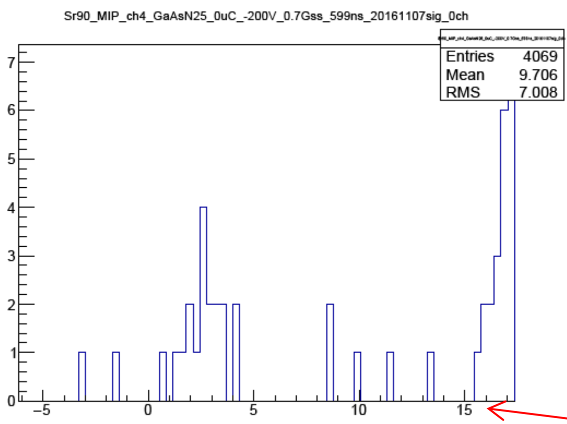
CCE, C $^{-2}$(left) and **σ** (right) as function of applied voltage for Si sensor after irradiation dose 602 kGy (2.5×10^{15} e^{-}/sm^{2}). Si N5 – type1, Si 6886 – type2.

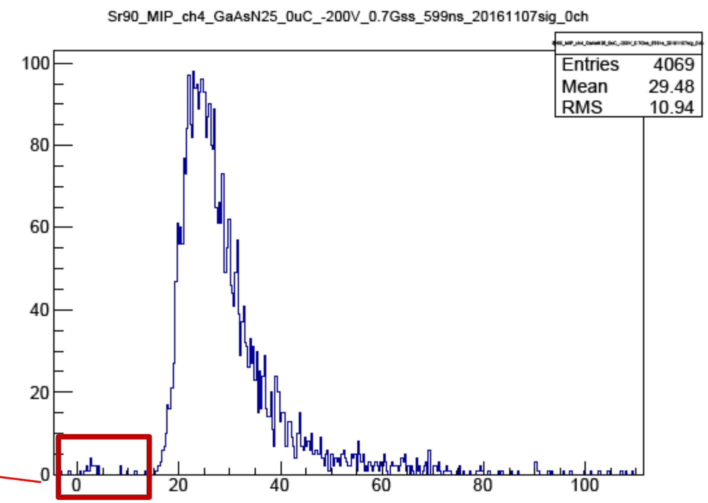
GaAs:Cr CCE - V_{bias} dependence.



For the irradiated GaAs:Cr sensors CCE increases significantly with the field strength up to **20 kV / cm**, while the unirradiated sensors reach saturation at **1 kV/cm**

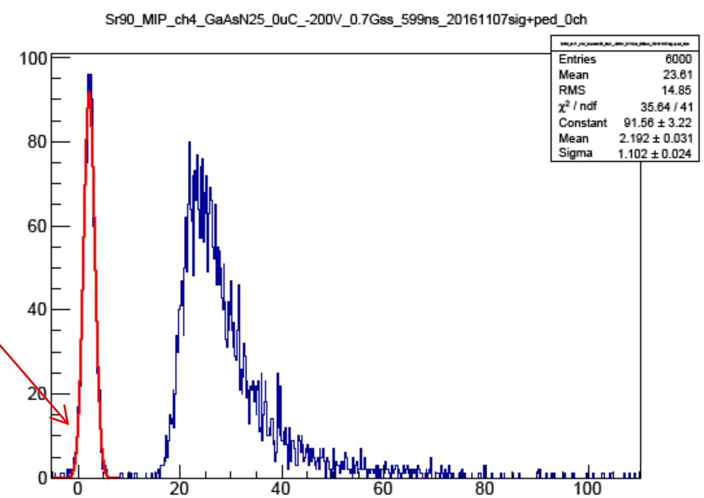
CCE measurement





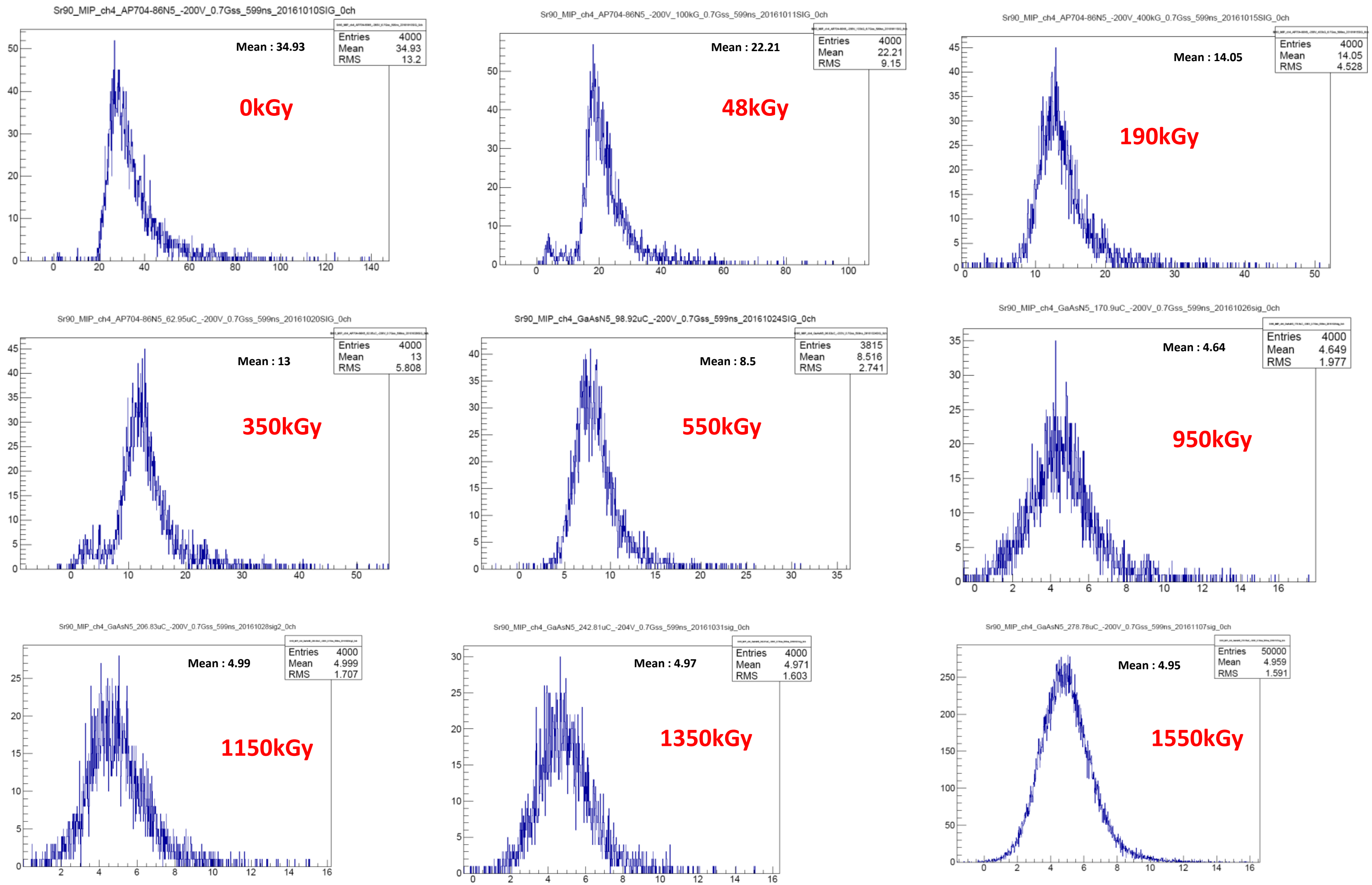
<0.5 % of pedestal in MIP spectrum

Pedestal of random trigger from generator

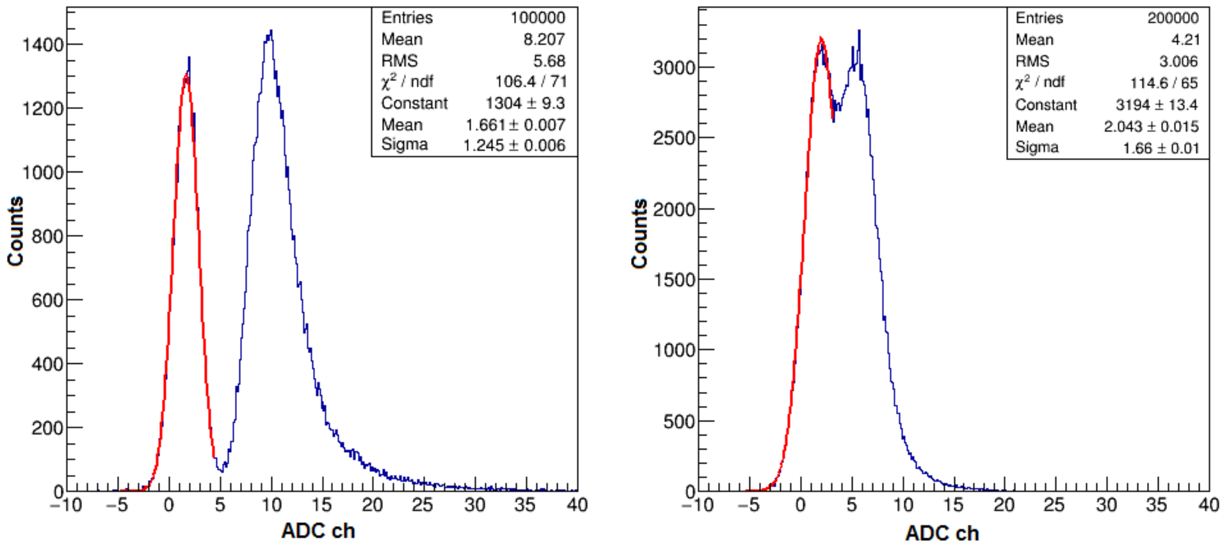


Collected Charge = Sig (MIP) – Ped

GaAs MIP signal vs Dose

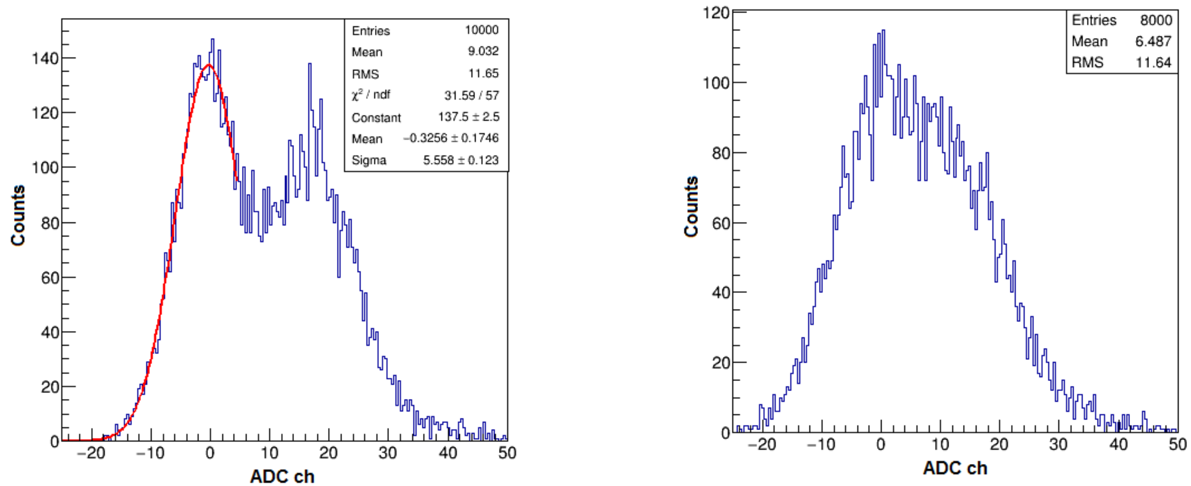


GaAs MIP signal vs Dose



MIP spectra for barrier GaAs:Cr N4 after irradiation dose 0.5 MGy (left) and GaAs:Cr N6 after 1.5MGy (right). Ubias=500V, the pedestal is visible on the left. Measurement temperature 21^{o}C.

Si MIP vs Dose



MIP spectra for Si_N5 (RIMST) after irradiation dose 0.5 MGy (left) and Si_N3 (RIMST) after 1.3 MGy (right). Ubias=100V, the pedestal is visible on the left. Measurement temperature 21^{o}C.

The pedestal expands and the signal from pedestal separation becomes difficult after doses 0.5MGy